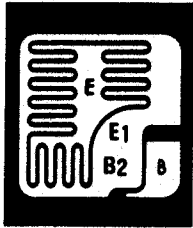


CHIP NUMBER

230



.099"
(2.52mm)

.095"
(2.41mm)

Output Base: .022" x .024" (0.56mm x 0.61mm)
 Input Base: .015" x .025" (0.38mm x 0.64mm)
 Output Emitter: .009" x .033" (0.23mm x 0.84mm)

PNP EPITAXIAL PLANAR POWER DARLINGTON (FORMERLY 30)**

CONTACT METALLIZATION

Base and emitter: > 30,000 Å Aluminum

Collector: Gold

(Polished silicon or "Chrome Nickel Silver" also available)

Also available on:

MOLY PEDESTAL

Size: .140 Diameter (3.56mm)

Thickness: .010" (0.25mm)

BeO PEDESTAL

Size: .142" x .178" (3.61mm x 4.52mm)

Thickness: .028" (0.71mm)

ASSEMBLY RECOMMENDATIONS

It is advisable that:

- a) the chip be eutectically mounted with gold silicon preform 98/2%.
- b) 8 mil (0.203mm) aluminum wire be ultrasonically attached to the base and emitter contacts.

TYPICAL ELECTRICAL CHARACTERISTICS AT 25°C

The following typical electrical characteristics apply for a completely finished component employing the chip number 230 in a TO-3 or equivalent case:

V _{CEO}	V _{CE(s)} @	I _C	I _B	h _{FE} @	I _C	V _{CE}
> 60V	< 2.2V	5A	50mA	> 1000	5A	5V
> 80V	< 2.2V	5A	50mA	> 1000	5A	5V
* > 100V	< 2.2V	5A	50mA	> 1000	5A	5V
* > 120V	< 2.2V	5A	50mA	> 500	5A	5V

V _{CEO}	V _{CEX}	V _{EBO}	f _T	C _{OBO}	θ _{JC}
> 60V	70V	> 10V	35MHz	< 60pF	< 2.0°C/W
> 80V	90V	> 10V	35MHz	< 60pF	< 2.0°C/W
> 100V	110V	> 10V	35MHz	< 60pF	< 2.0°C/W
> 120V	130V	> 10V	35MHz	< 60pF	< 2.0°C/W

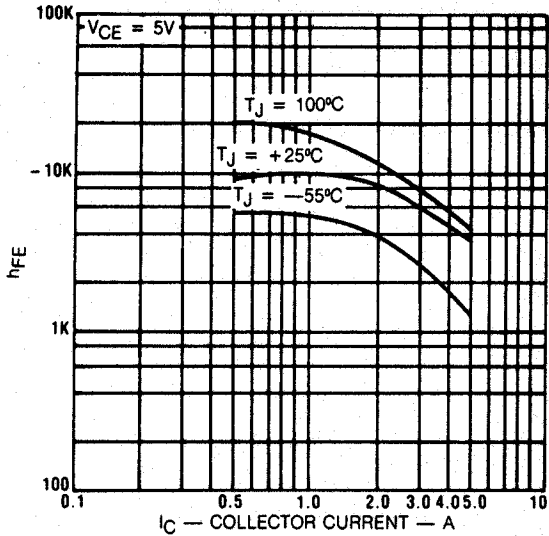
TYPICAL DEVICE TYPES: SDM3400 - SDM3405, SDM3200 - SDM3205

*h_{FE} available at I_C = 1A, V_{CE} = 5.0V, > 1000

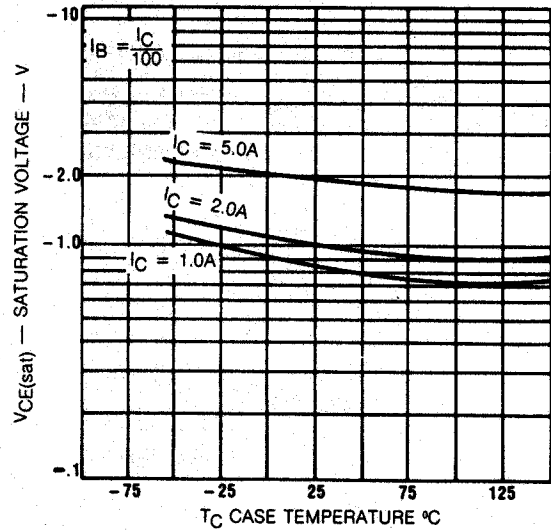
**The respective NPN complement is chip number 103.

MEDIUM VOLTAGE, FAST SWITCHING, HIGH GAIN CHIP TYPE 230

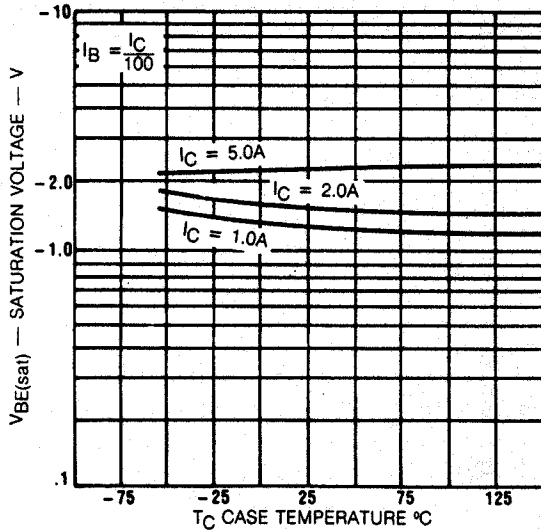
TYPICAL STATIC FORWARD CURRENT TRANSFER RATIO



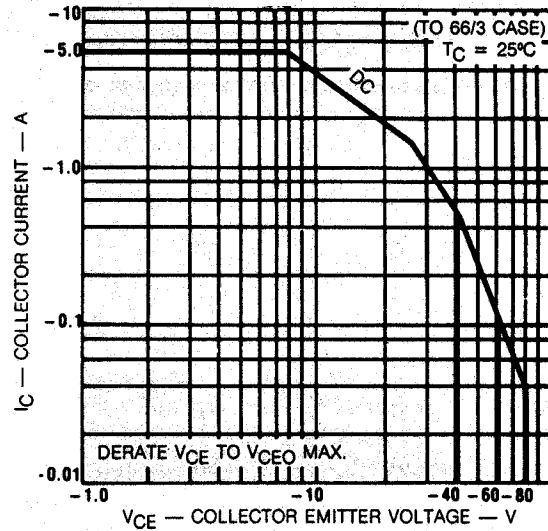
TYPICAL COLLECTOR EMITTER SATURATION VOLTAGE



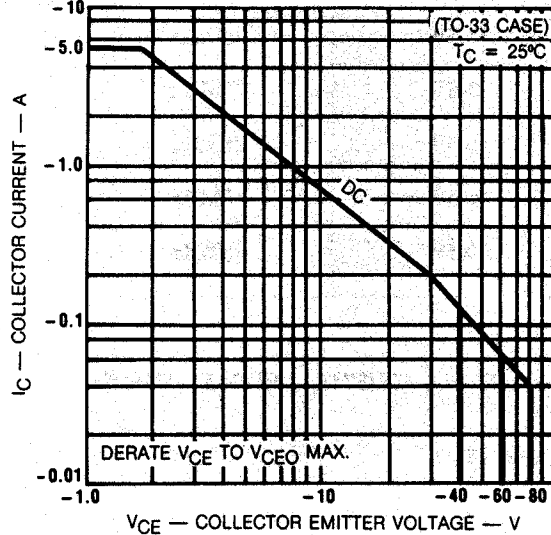
TYPICAL BASE EMITTER SATURATION VOLTAGE



MAXIMUM OPERATING CONDITIONS



MAXIMUM OPERATING CONDITIONS



NOTE:
PERFORMANCE CURVES
REPRESENT LOW TO
MIDDLE CEO VOLTAGE
RANGE OF THIS PRODUCT